1. General description

NPN low V_{CEsat} Breakthrough in a Small Signal (BISS) transistor, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and soldarable side pads.

PNP complement: PBSS5360PAS

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High efficiency due to less heat generation
- · High temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) area requirements
- · Leadless small SMD plastic package with soldarable side pads
- · Exposed heat sink for excellent thermal and electrical conductivity
- · Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- · Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	60	V
I _C	collector current		-	-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	6	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	73	108	mΩ



60 V, 3 A NPN low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	Е	emitter		С
3	С	collector	1 2 Transparent top view	B E sym021
			DFN2020D-3 (SOT1061D)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS4360PAS	DFN2020D-3	plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); no leads; 3 terminals; 1.3 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1061D			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4360PAS	E9

60 V, 3 A NPN low VCEsat (BISS) transistor

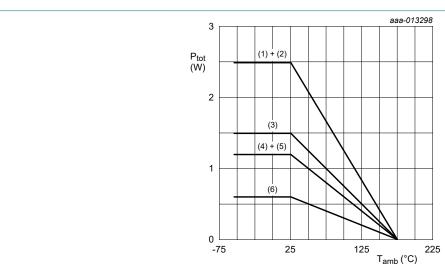
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	80	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
Ic	collector current			-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	6	А
I _B	base current			-	500	mA
I _{BM}	peak base current			-	1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2] [3]	-	1.2	W
			[4]	-	1.5	W
			[5] [6]	-	2.5	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².



- (1) Ceramic PCB, single-sided copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm²
- (3) FR4 PCB, single-sided copper, 6 cm²
- (4) FR4 PCB, single-sided copper, 1 cm²
- (5) FR4 PCB, 4-layer copper, standard footprint
- (6) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

60 V, 3 A NPN low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	in free air	[1]	-	-	250	K/W
	junction to ambient	[2] [3]	-	-	125	K/W	
		[4]	-	-	100	K/W	
			[5] [6]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm²
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Device mounted on a FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².

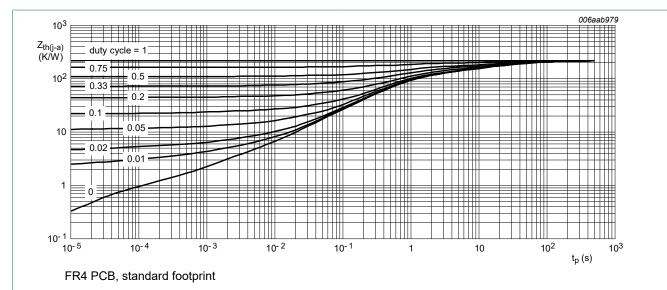


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

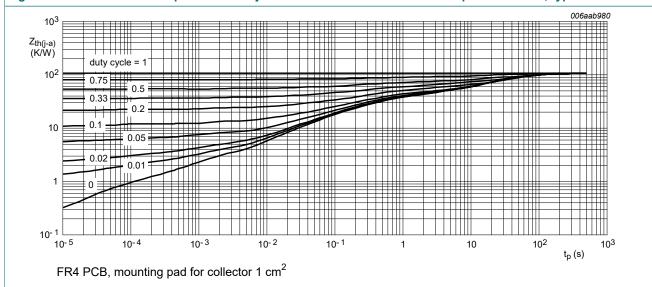


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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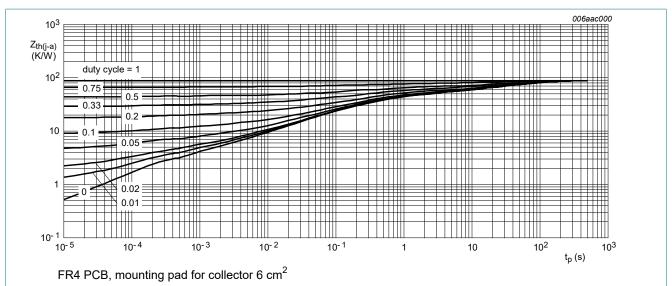
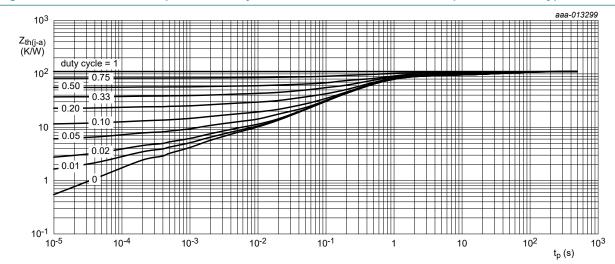
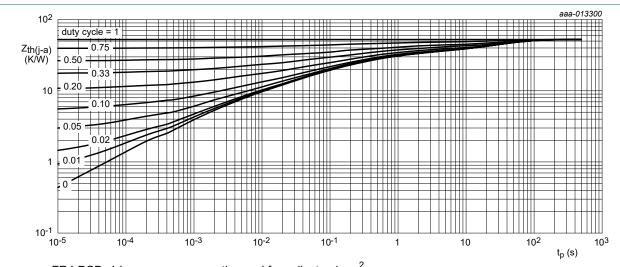


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, standard footprint

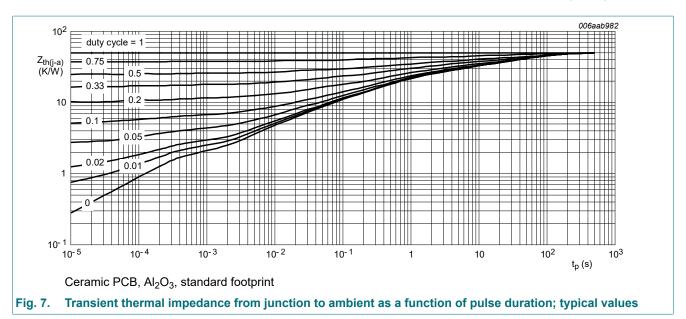
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, mounting pad for collector 1 cm²

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 3 A NPN low VCEsat (BISS) transistor



60 V, 3 A NPN low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{СВО}	collector-base cut-off	V _{CB} = 64 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
current		V _{CB} = 64 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
CES	collector-emitter cut-off current	V _{CE} = 48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
EBO	emitter-base cut-off current	$V_{EB} = 5.6 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
) _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 0.05 A; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	200	380	-	
		V_{CE} = 5 V; I_{C} = 0.5 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	360	-	
		V_{CE} = 5 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	200	330	-	
		V_{CE} = 5 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	125	220	-	
		V_{CE} = 5 V; I_{C} = 3 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	75	140	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 0.5 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	45	60	mV
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	80	110	mV
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	150	210	mV
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$	-	220	325	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	73	108	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 2 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.9	1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 5 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	0.75	0.95	V
d	delay time	I _C = 2 A; I _{Bon} = 0.1 A; I _{Boff} = -0.1 A;	-	11	-	ns
r	rise time	T _{amb} = 25 °C	-	130	-	ns
on	turn-on time		-	141	-	ns
·s	storage time		-	200	-	ns
f	fall time		-	110	-	ns
· ·off	turn-off time		-	310	-	ns
fт	transition frequency	V _{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	75	160	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	11	14	pF

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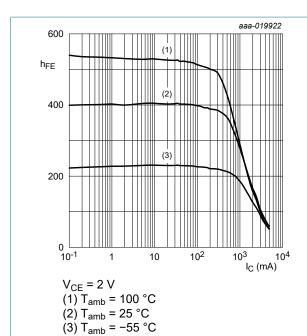


Fig. 8. DC current gain as a function of collector current; typical values

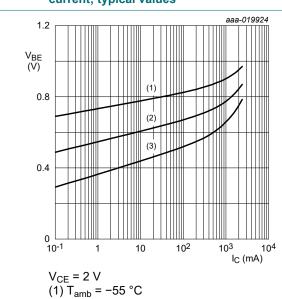


Fig. 10. Base-emitter voltage as a function of collector current; typical values

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

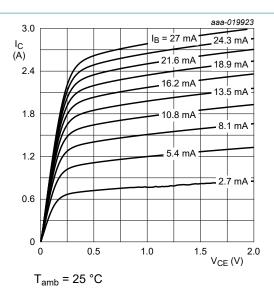
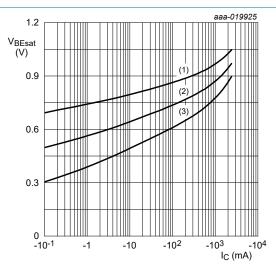


Fig. 9. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values

60 V, 3 A NPN low VCEsat (BISS) transistor

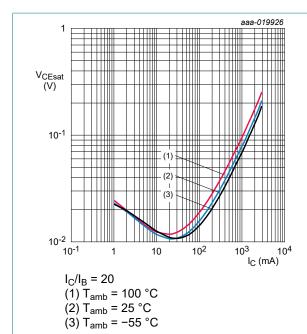


Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

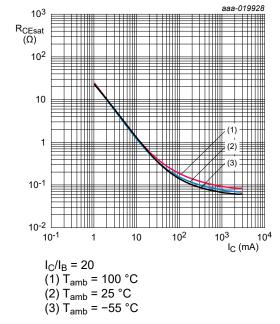


Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values

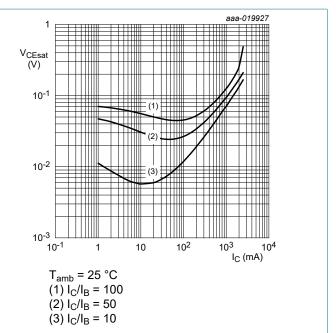


Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values

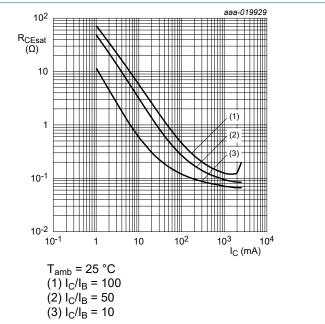
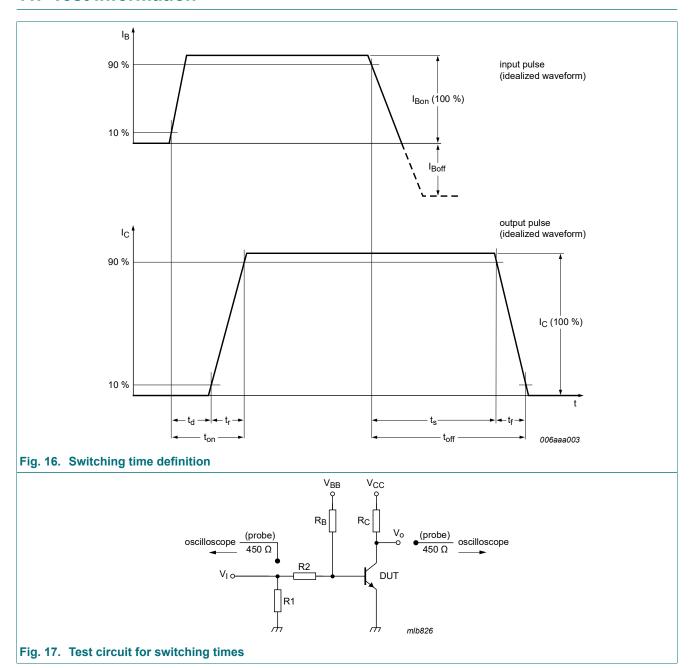


Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



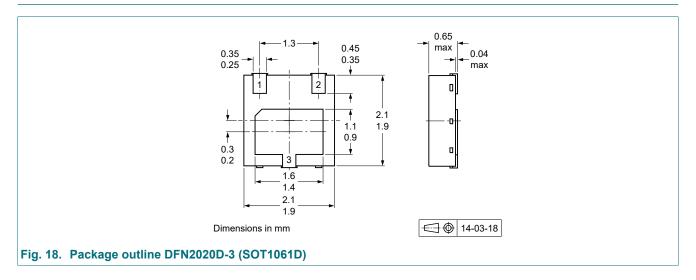
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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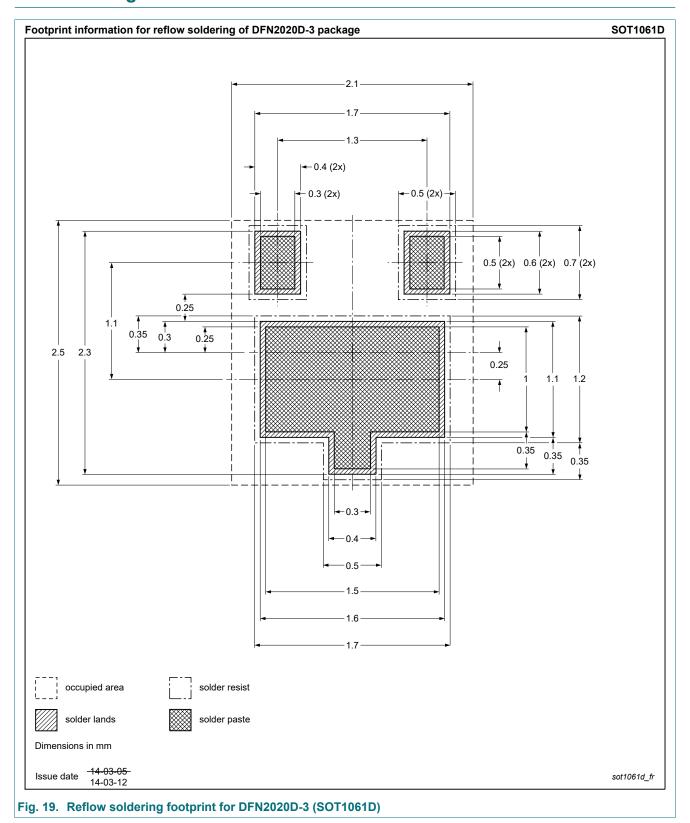
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS4360PAS v.2	20220318	Product data sheet	-	PBSS4360PAS v.1			
Modifications:	Nexperia.	The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate.					
PBSS4360PAS v.1	20151016	Product data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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